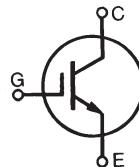


GenX3™ 1200V IGBTs

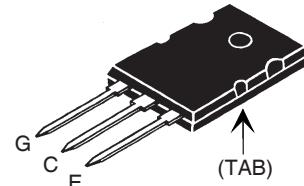
IXGK120N120B3
IXGX120N120B3

High Speed Low V_{sat} PT IGBTs
for 3-20 kHz Switching

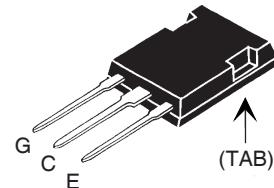


V_{CES} = 1200V
 I_{C90} = 120A
 $V_{CE(sat)}$ ≤ 3.0V

TO-264 (IXGK)



PLUS 247™ (IXGX)



G = Gate E = Emitter
C = Collector TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	1200	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	1200	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	200	A
I_{C90}	T_C = 90°C	120	A
I_{LRMS}	Terminal Current Limit	120	A
I_{CM}	T_C = 25°C, 1ms	370	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{vj} = 125^{\circ}C$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{OM} = 240$ $V_{CES} \leq 1200$	A V
P_c	T_C = 25°C	830	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	°C
M_d	Mounting Torque (IXGK)	1.13/10	Nm/lb.in.
F_c	Mounting Force (IXGX)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{CE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 1mA$, $V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^{\circ}C$		50 μA 5 mA	
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		±400 nA	
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1	2.4	3.0	V

Features

- Optimized for Low Conduction and Switching Losses
- Square RBSOA
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	40	70	S
C_{ies}		9700		pF
C_{oes}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1 \text{ MHz}$	670		pF
C_{res}		255		pF
$Q_{g(on)}$		470		nC
Q_{ge}	$I_C = I_{C90}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$	67		nC
Q_{gc}		190		nC
$t_{d(on)}$		36		ns
t_{ri}	Inductive load, $T_J = 25^\circ\text{C}$	88		ns
E_{on}	$I_C = 100\text{A}, V_{GE} = 15\text{V}$	5.5		mJ
$t_{d(off)}$	$V_{CE} = 600\text{V}, R_G = 2\Omega$	275		ns
t_{fi}	Note 2	145		ns
E_{off}		5.8		mJ
$t_{d(on)}$		34		ns
t_{ri}	Inductive load, $T_J = 125^\circ\text{C}$	88		ns
E_{on}	$I_C = 100\text{A}, V_{GE} = 15\text{V}$	6.1		mJ
$t_{d(off)}$	$V_{CE} = 600\text{V}, R_G = 2\Omega$	315		ns
t_{fi}	Note 2	570		ns
E_{off}		10.3		mJ
R_{thJC}			0.15	$^\circ\text{C}/\text{W}$
R_{thCK}			0.15	$^\circ\text{C}/\text{W}$

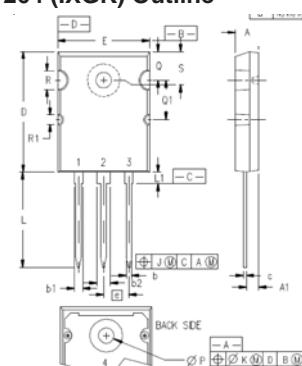
Note

1. Pulse Test, $t \leq 300\mu\text{s}$, Duty Cycle, $d \leq 2\%$.
2. Switching Times may Increase for V_{CE} (Clamp) $> 0.8 V_{CES}$, Higher T_J or Increased R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

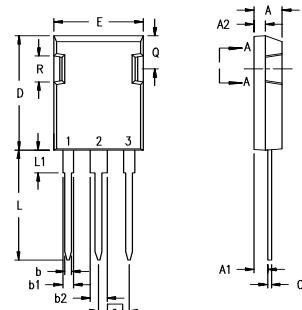
TO-264 (IXGK) Outline



1 - GATE
2, 4 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS 247™ (IXGX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

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